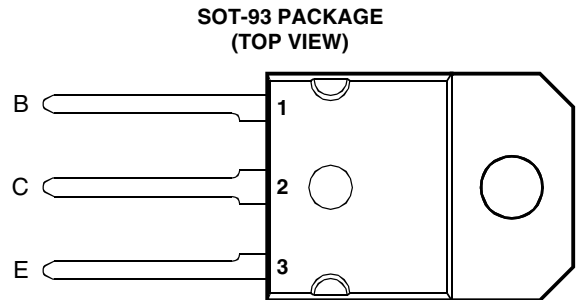


- Designed for Complementary Use with the BD249 Series
- 125 W at 25°C Case Temperature
- 25 A Continuous Collector Current
- 40 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-emitter voltage ($R_{BE} = 100 \Omega$)	BD250	V_{CER}	-55	V
	BD250A		-70	
	BD250B		-90	
	BD250C		-115	
Collector-emitter voltage ($I_C = -30 \text{ mA}$)	BD250	V_{CEO}	-45	V
	BD250A		-60	
	BD250B		-80	
	BD250C		-100	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-25	A
Peak collector current (see Note 1)		I_{CM}	-40	A
Continuous base current		I_B	-5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	125	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	90	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

NOTES: 1. This value applies for $t_p \leq 0.3 \text{ ms}$, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 24 mW/°C.
 4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20 \text{ mH}$, $I_{B(on)} = -0.4 \text{ A}$, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = -20 \text{ V}$.

PRODUCT INFORMATION

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BD250, BD250A, BD250B, BD250C

PNP SILICON POWER TRANSISTORS

BOURNS®

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -30 \text{ mA}$ (see Note 5)	$I_B = 0$	BD250 BD250A BD250B BD250C	-45 -60 -80 -100			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = -55 \text{ V}$ $V_{CE} = -70 \text{ V}$ $V_{CE} = -90 \text{ V}$ $V_{CE} = -115 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	BD250 BD250A BD250B BD250C			-0.7 -0.7 -0.7 -0.7	mA
I_{CEO} Collector cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_B = 0$ $I_B = 0$	BD250/250A BD250B/250C			-1 -1	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$				-1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$	$I_C = -1.5 \text{ A}$ $I_C = -15 \text{ A}$ $I_C = -25 \text{ A}$	(see Notes 5 and 6)	25 10 5			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -1.5 \text{ A}$ $I_B = -5 \text{ A}$	$I_C = -15 \text{ A}$ $I_C = -25 \text{ A}$	(see Notes 5 and 6)			-1.8 -4	V
V_{BE} Base-emitter voltage	$V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$	$I_C = -15 \text{ A}$ $I_C = -25 \text{ A}$	(see Notes 5 and 6)			-2 -4	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -1 \text{ A}$	$f = 1 \text{ kHz}$	25			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -1 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			42	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -5 \text{ A}$	$I_{B(on)} = -0.5 \text{ A}$	$I_{B(off)} = 0.5 \text{ A}$		0.2		μs
t_{off} Turn-off time	$V_{BE(off)} = 5 \text{ V}$	$R_L = 5 \Omega$	$t_p = 20 \mu\text{s}$, dc $\leq 2\%$		0.4		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PRODUCT INFORMATION

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TYPICAL CHARACTERISTICS

**TYPICAL DC CURRENT GAIN
vs
COLLECTOR CURRENT**

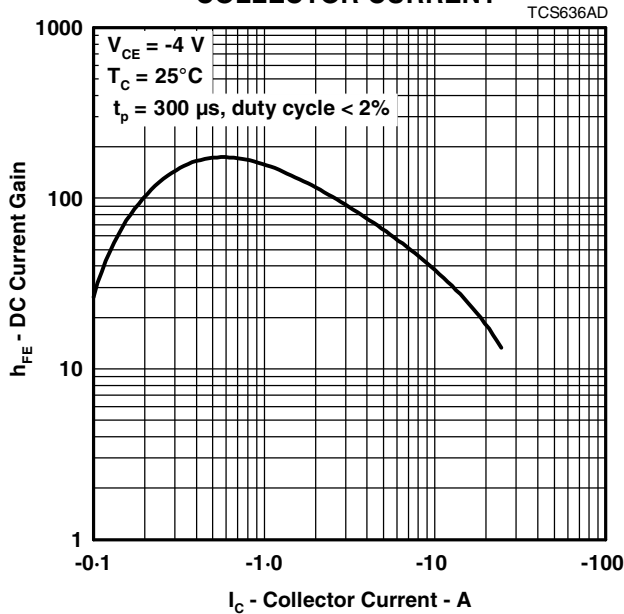


Figure 1.

**COLLECTOR-EMITTER SATURATION VOLTAGE
vs
BASE CURRENT**

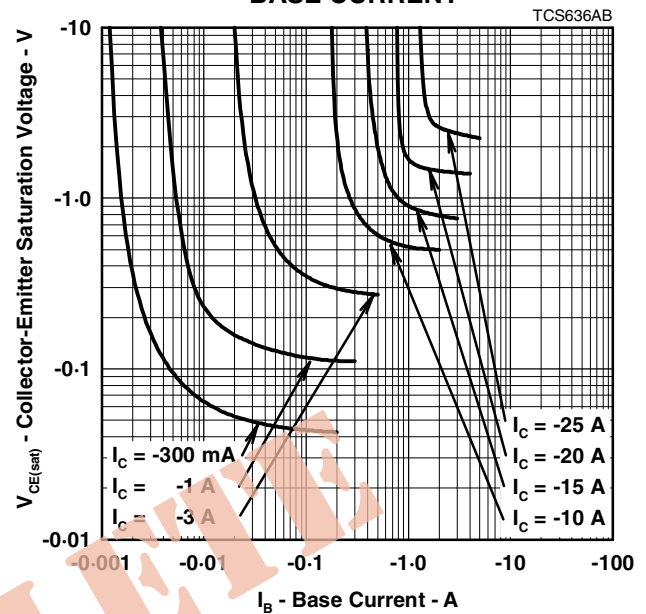


Figure 2.

**BASE-EMITTER VOLTAGE
vs
COLLECTOR CURRENT**

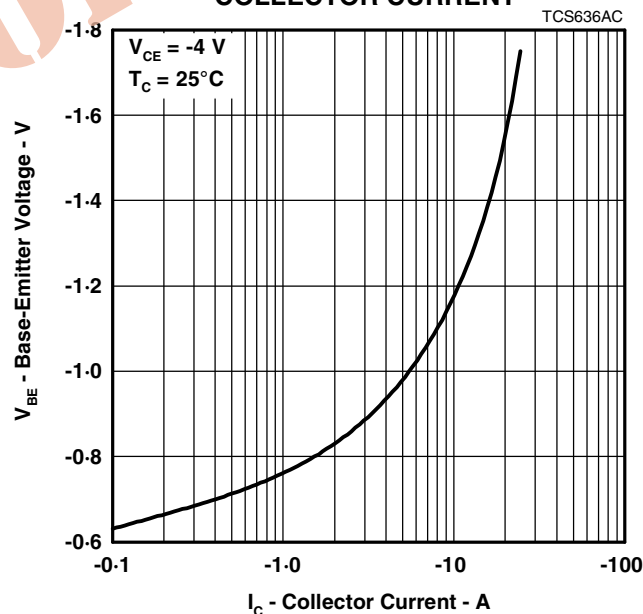


Figure 3.

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MAXIMUM SAFE OPERATING REGIONS

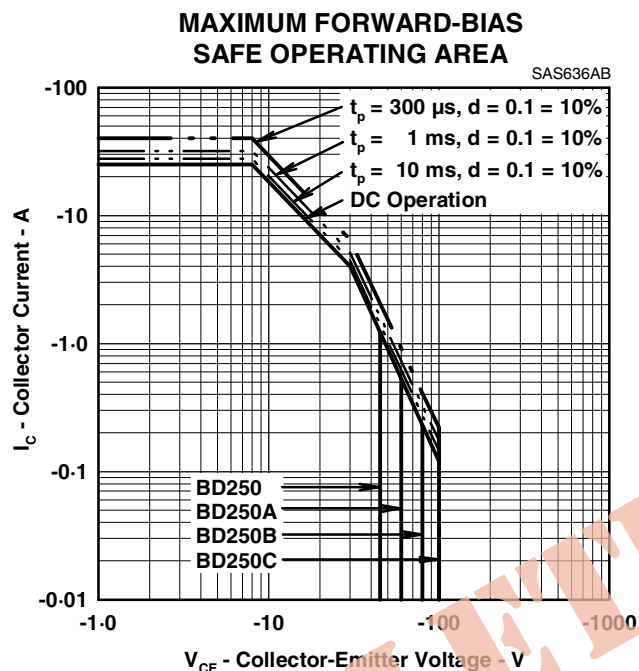


Figure 4.

THERMAL INFORMATION

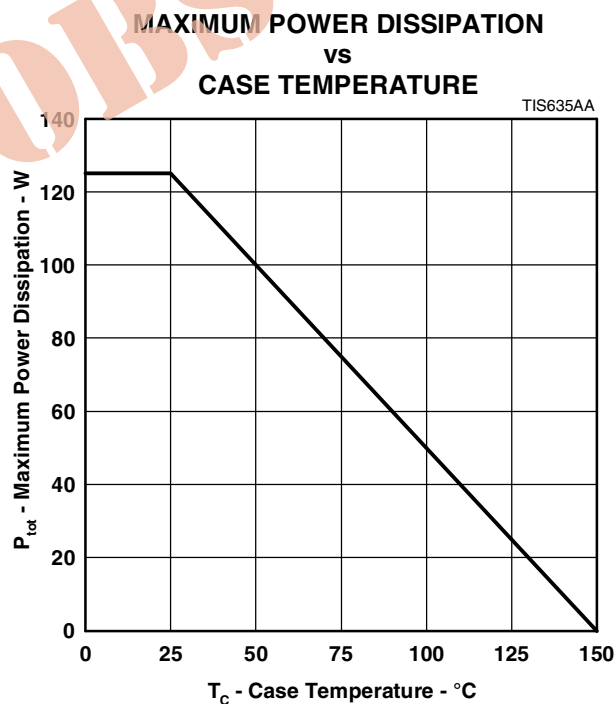


Figure 5.

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